

# NTMFS4744N

## Power MOSFET

30 V, 53 A, Single N-Channel, SO-8 FL

### Features

- Low RDS(on) to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These are Pb-Free Devices

### Applications

- CPU Power Delivery
- DC-DC Converters
- Low Side Switching

### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise stated)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>	30	V
Gate-to-Source Voltage	V <sub>GS</sub>	20	V
Continuous Drain Current R <sub>θJA</sub> (Note 1)	I <sub>D</sub>	T <sub>A</sub> = 25°C	11
		T <sub>A</sub> = 85°C	8.0
Power Dissipation R <sub>θJA</sub> (Note 1)	P <sub>D</sub>	2.2	W
Continuous Drain Current R <sub>θJA</sub> (Note 2)	I <sub>D</sub>	T <sub>A</sub> = 25°C	7.0
		T <sub>A</sub> = 85°C	5.0
Power Dissipation R <sub>θJA</sub> (Note 2)	P <sub>D</sub>	0.88	W
Continuous Drain Current R <sub>θJC</sub> (Note 1)	I <sub>D</sub>	T <sub>C</sub> = 25°C	53
		T <sub>C</sub> = 85°C	38
Power Dissipation R <sub>θJC</sub> (Note 1)	P <sub>D</sub>	47.2	W
Pulsed Drain Current	I <sub>DM</sub>	106	A
Operating Junction and Storage Temperature	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C
Source Current (Body Diode)	I <sub>S</sub>	46	A
Drain to Source dV/dt	dV/dt	6.0	V/ns
Single Pulse Drain-to-Source Avalanche Energy (V <sub>DD</sub> = 50 V, V <sub>GS</sub> = 10 V, I <sub>L</sub> = 24 A <sub>pk</sub> , L = 1.0 mH, R <sub>G</sub> = 25 Ω)	EAS	286	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T <sub>L</sub>	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

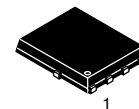
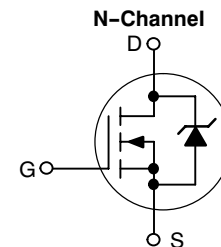


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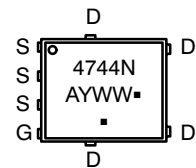
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V <sub>(BR)DSS</sub>	RDS(on) MAX	I <sub>D</sub> MAX
30 V	10 mΩ @ 10 V	53 A
	14 mΩ @ 4.5 V	



SO-8 FLAT LEAD  
CASE 488AA  
STYLE 1

### MARKING DIAGRAM



4744N = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
NTMFS4744NT1G	SO-8 FL (Pb-Free)	1500 Tape & Reel
NTMFS4744NT3G	SO-8 FL (Pb-Free)	5000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	2.65	°C/W
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	56.9	
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	142.4	

- Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
- Surface-mounted on FR4 board using the minimum recommended pad size.

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## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			10		mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	$\mu\text{A}$
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

### ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	1.5		2.5	V	
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			5.0		mV/°C	
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V to } 11.5\text{ V}$	$I_D = 30\text{ A}$		7.6	m $\Omega$	
			$I_D = 15\text{ A}$		7.3		
			$I_D = 10\text{ A}$		7.3		10
		$V_{GS} = 4.5\text{ V}$	$I_D = 30\text{ A}$		10.4		
			$I_D = 15\text{ A}$		10.1		
			$I_D = 10\text{ A}$		9.9		14
Forward Transconductance	$g_{FS}$	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$		25		S	

### CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 12\text{ V}$		1300		pF
Output Capacitance	$C_{OSS}$			550		
Reverse Transfer Capacitance	$C_{RSS}$			132		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		10	17	nC
Threshold Gate Charge	$Q_{G(TH)}$			0.9		
Gate-to-Source Charge	$Q_{GS}$			1.8		
Gate-to-Drain Charge	$Q_{GD}$			5.9		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 11.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		25	37	nC

### SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 30\text{ A}, R_G = 3.0\ \Omega$		12		ns
Rise Time	$t_r$			203		
Turn-Off Delay Time	$t_{d(OFF)}$			14		
Fall Time	$t_f$			83		

- Pulse Test: pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Switching characteristics are independent of operating junction temperatures.

# NTMFS4744N

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>SWITCHING CHARACTERISTICS</b> (Note 4)						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 11.5\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 30\text{ A}, R_G = 3.0\ \Omega$		7.0		ns
Rise Time	$t_r$			94		
Turn-Off Delay Time	$t_{d(OFF)}$			23		
Fall Time	$t_f$			4.7		

## DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V},$ $I_S = 30\text{ A}$	$T_J = 25^\circ\text{C}$		0.78	1.2	V
			$T_J = 125^\circ\text{C}$		0.7		
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 30\text{ A}$		37	60	ns	
Charge Time	$t_a$			21			
Discharge Time	$t_b$			17			
Reverse Recovery Charge	$Q_{RR}$			37		nC	

## PACKAGE PARASITIC VALUES

Source Inductance	$L_S$	$T_A = 25^\circ\text{C}$		0.65		nH
Drain Inductance	$L_D$			0.005		
Gate Inductance	$L_G$			1.84		
Gate Resistance	$R_G$			2.0	5.0	

- Pulse Test: pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Switching characteristics are independent of operating junction temperatures.

# NTMFS4744N

## TYPICAL PERFORMANCE CURVES

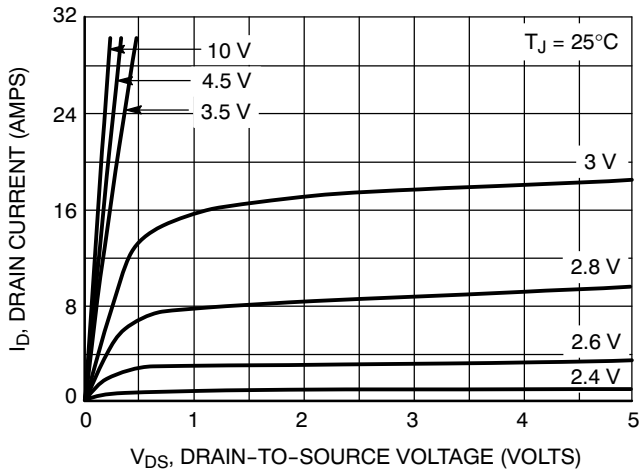


Figure 1. On-Region Characteristics

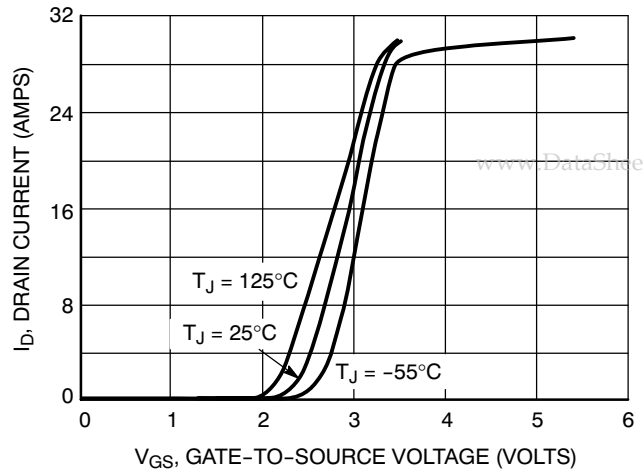


Figure 2. Transfer Characteristics

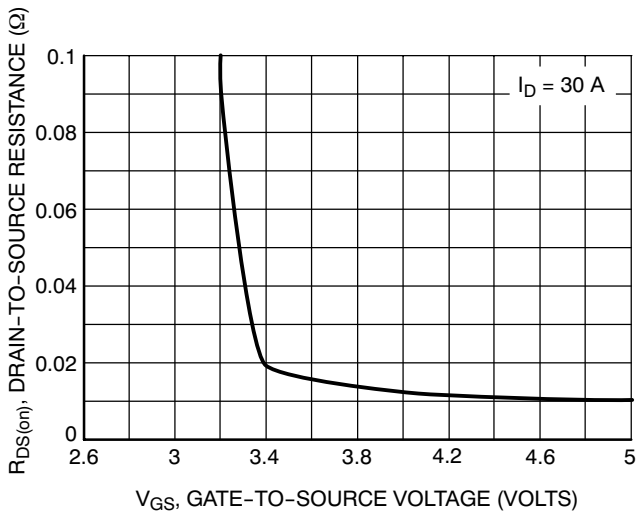


Figure 3. On-Resistance vs. Gate-to-Source Voltage

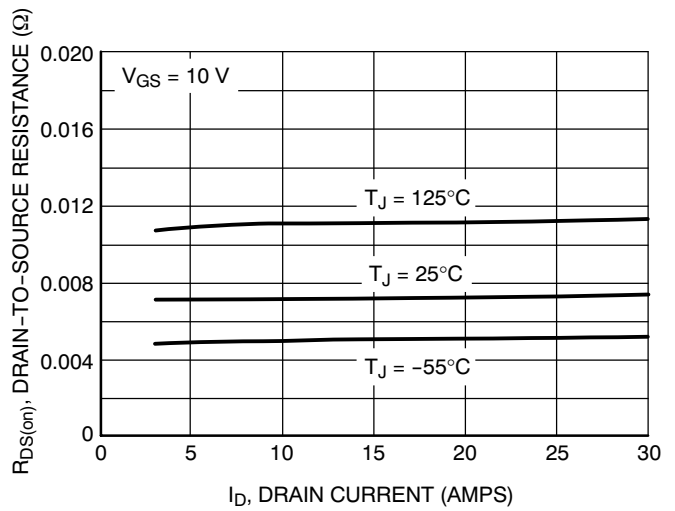


Figure 4. On-Resistance vs. Drain Current and Temperature

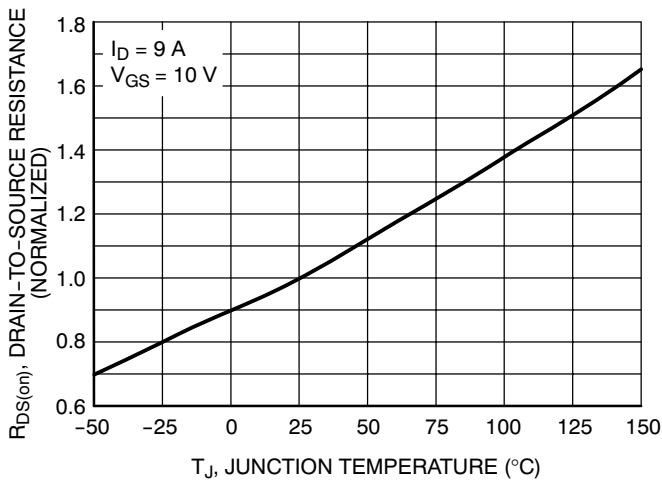


Figure 5. On-Resistance Variation with Temperature

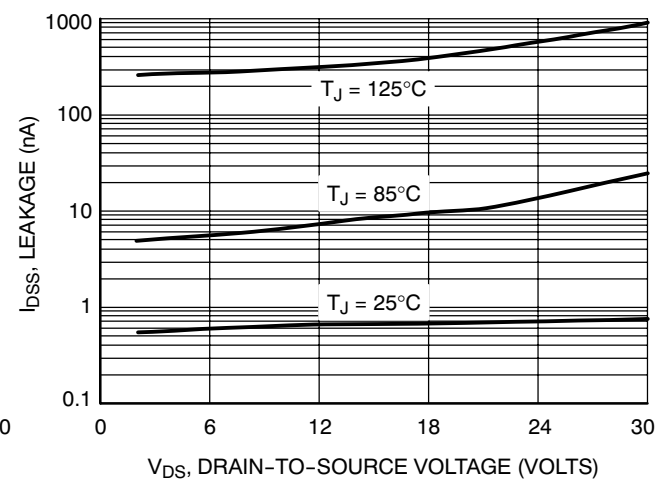


Figure 6. Drain-to-Source Leakage Current vs. Drain Voltage

TYPICAL PERFORMANCE CURVES

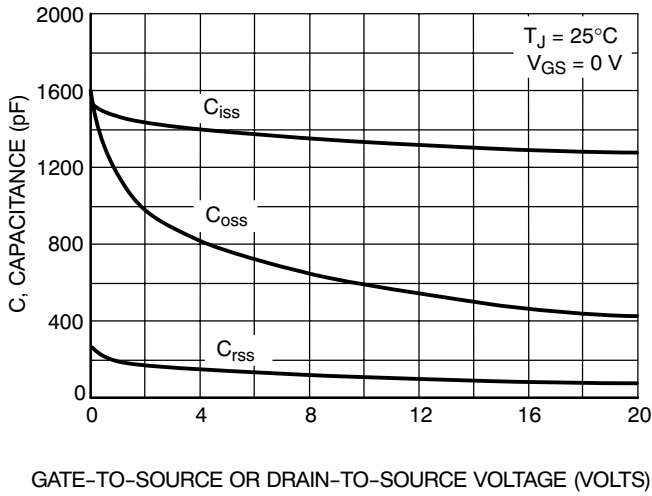


Figure 7. Capacitance Variation

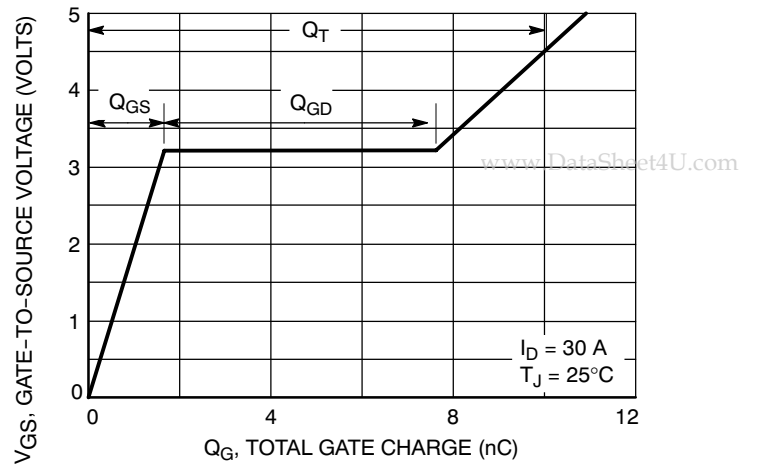


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

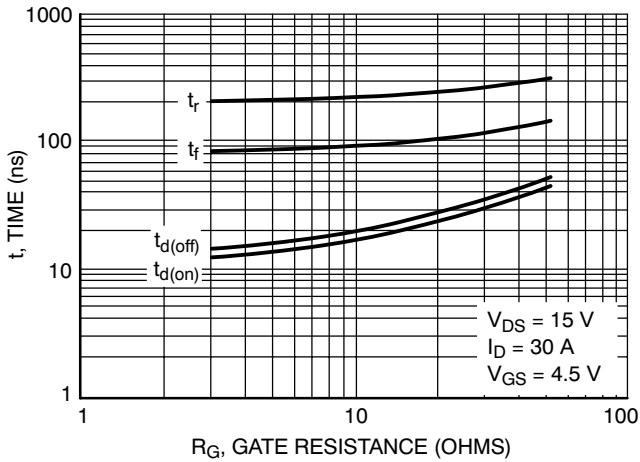


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

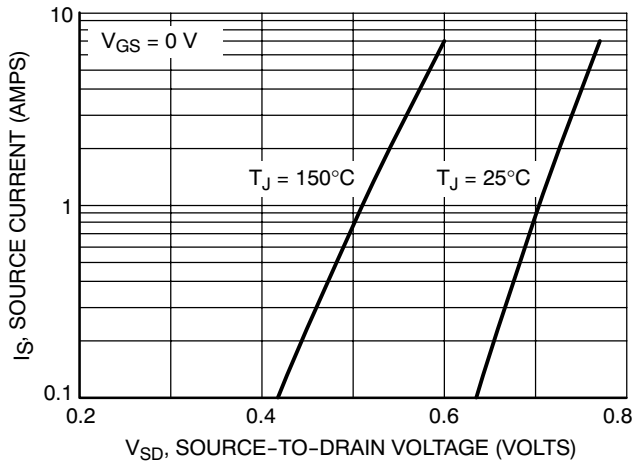


Figure 10. Diode Forward Voltage vs. Current

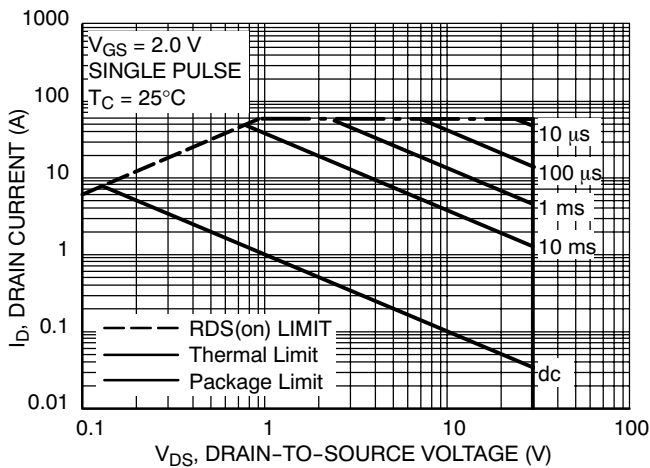


Figure 11. Maximum Rated Forward Biased Safe Operating Area

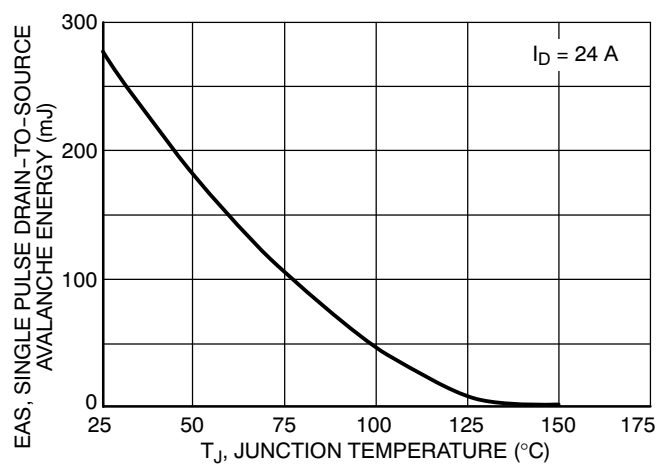
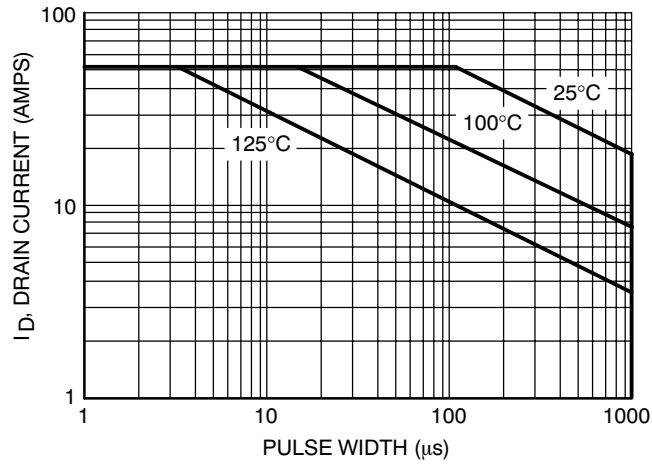


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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## TYPICAL PERFORMANCE CURVES



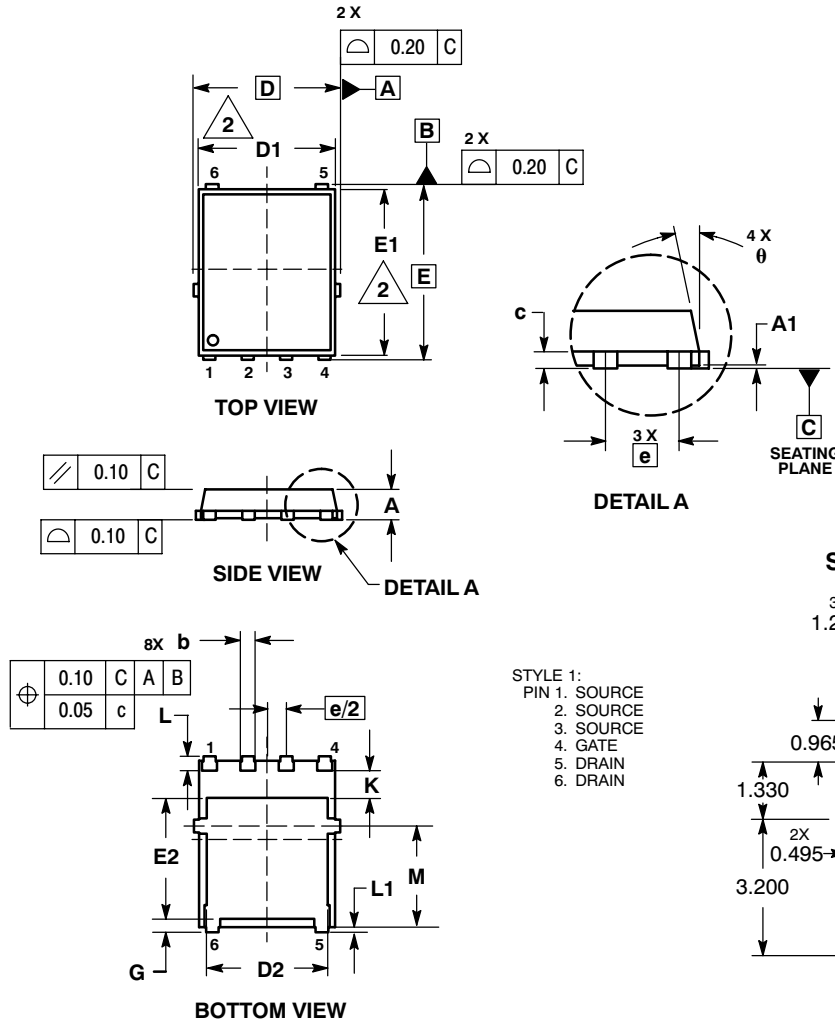
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Figure 13. Avalanche Characteristics

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## PACKAGE DIMENSIONS

DFN6 5x6, 1.27P (SO8 FL)  
CASE 488AA-01  
ISSUE C

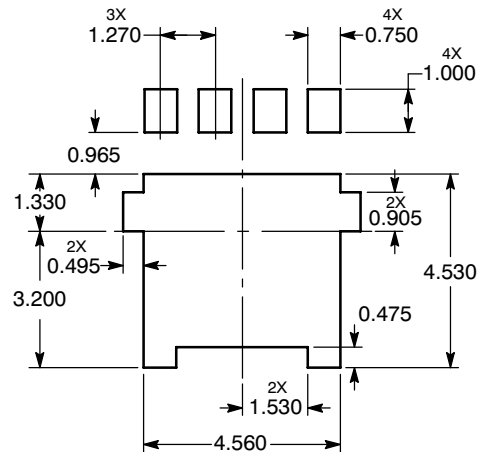


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.15 BSC		
D1	4.50	4.90	5.10
D2	3.50	---	4.22
E	6.15 BSC		
E1	5.50	5.80	6.10
E2	3.45	---	4.30
e	1.27 BSC		
G	0.51	0.61	0.71
K	0.51	---	---
L	0.51	0.61	0.71
L1	0.05	0.17	0.20
M	3.00	3.40	3.80
θ	0°	---	12°

**SOLDERING FOOTPRINT\***



- STYLE 1:  
PIN 1. SOURCE  
2. SOURCE  
3. SOURCE  
4. GATE  
5. DRAIN  
6. DRAIN

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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